Switch-mode Power Rectifier 150 V, 10 A

MBRF10H150CTG

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capability
- 10 A Total (5 A Per Diode Leg)
- Guard-Ring for Stress Protection
- This is a Pb-Free Device

Applications

- Power Supply Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight (Approximately): 1.9 Grams
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

MAXIMUM RATINGS

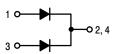
Please See the Table on the Following Page

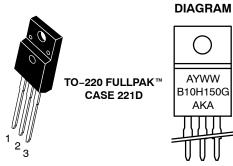


ON Semiconductor®

www.onsemi.com

SCHOTTKY BARRIER RECTIFIER 10 AMPERES, 150 VOLTS





MARKING

= Assembly Location

= Year WW = Work Week B10H150 = Device Code = Pb-Free Device **AKA** = Polarity Designator

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MBRF10H150CTG

MAXIMUM RATINGS (Per Diode Leg)

Rating		Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	150	V
Average Rectified Forward Current (Per Leg) (Rated V_R) $T_C = 142^{\circ}C$ (Per Device)	I _{F(AV)}	5 10	Α
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I _{FSM}	150	Α
Operating Junction Temperature (Note 1)	T _J	-20 to +150	°C
Storage Temperature	T _{stg}	-65 to +150	°C
Voltage Rate of Change (Rated V _R)	dv/dt	10000	V/μs
ESD Ratings: Machine Model = C Human Body Model = 3B		> 400 > 8000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating		Symbol	Value	Unit
Maximum Thermal Resistance	Junction-to-Case	$R_{ heta JC}$	2.5	°C/W

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Rating	Symbol	Тур	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2) $ (I_F = 5 \text{ A, T}_C = 25^\circ\text{C}) \\ (I_F = 5 \text{ A, T}_C = 125^\circ\text{C}) $	VF	0.85 0.63	0.69	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, T_C = 25°C) (Rated DC Voltage, T_C = 125°C)	İR		45 20	μA mA

^{2.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

DEVICE ORDERING INFORMATION

Device Order Number	Package Type	Shipping [†]
MBRF10H150CTG	TO-220FP (Pb-Free)	50 Units / Rail

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

^{1.} The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

MBRF10H150CTG

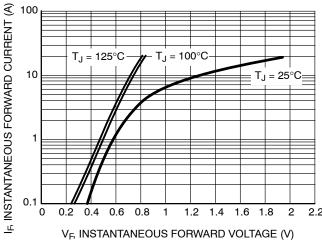


Figure 1. Typical Forward Voltage

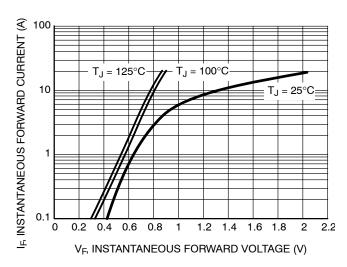


Figure 2. Maximum Forward Voltage

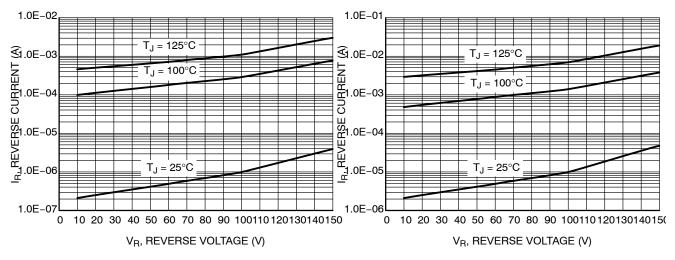


Figure 3. Typical Reverse Current

Figure 4. Maximum Reverse Current

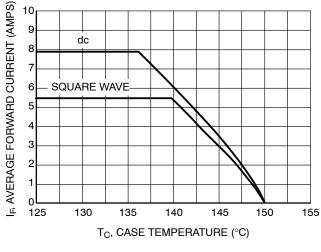


Figure 5. Current Derating

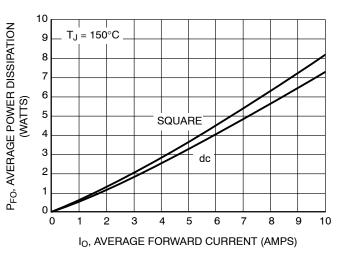
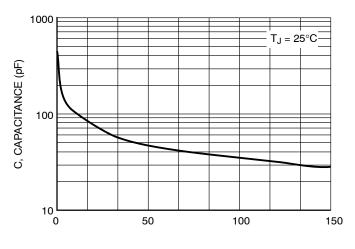


Figure 6. Forward Power Dissipation

MBRF10H150CTG



V_R, REVERSE VOLTAGE (V)

Figure 7. Capacitance

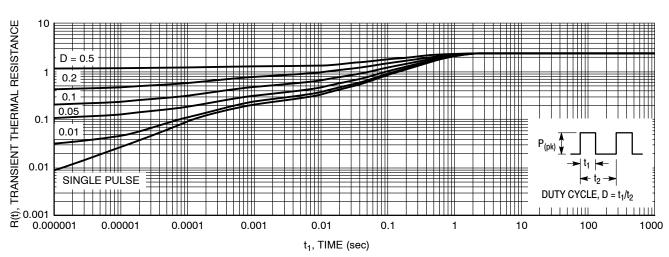


Figure 8. Thermal Response Junction-to-Case for MBRF10H150CTG

MECHANICAL CASE OUTLINE





SCALE 1:1

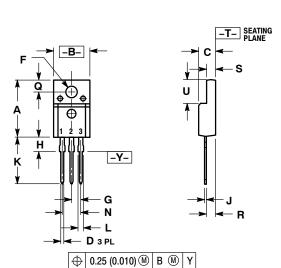
TO-220 FULLPAK CASE 221D-03 ISSUE K

DATE 27 FEB 2009



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH
- 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.617	0.635	15.67	16.12
В	0.392	0.419	9.96	10.63
C	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100 BSC		2.54 BSC	
Н	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200 BSC		5.08	BSC
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88



MARKING DIAGRAMS

STYLE 1: PIN 1. GATE 2. DRAIN 3. SOURCE

STYLE 4: PIN 1. CATHODE

3. CATHODE

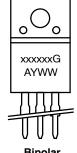
ANODE

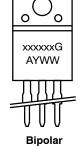
STYLE 2: PIN 1. BASE 2. COLLECTOR 3. EMITTER 2.

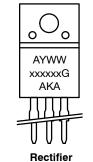
STYLE 6: PIN 1. MT 1 2. MT 2 3. GATE STYLE 5: PIN 1. CATHODE 2. ANODE 3. GATE

STYLE 3: PIN 1. ANODE

CATHODE
 ANODE







= Assembly Location xxxxxx = Specific Device Code G = Pb-Free Package Υ = Year

= Assembly Location WW = Work Week = Year XXXXXX = Device Code = Work Week = Pb-Free Package WW G AKA = Polarity Designator

DOCUMENT NUMBER:	98ASB42514B	Electronic versions are uncontrolled except when accessed directly from the Document Repository Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	TO-220 FULLPAK		PAGE 1 OF 1

Α

Υ

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and the are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative